The picture shows an FIB cross section through a defective aluminum contact structure. In the silicon-substrate, under the contact, a perfect geometric shaped material interdiffusion (Al-Si) could be found.

Photo by Susanne Hübner, Fraunhofer Institute for Mechanics of Materials
3rd Place: black and white images
EDFAS 2011 Photo Contest
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First printing, November 2012

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SAN: 204-7586

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